

SANYO

No.2360

LC3516A,AM,AS/LC3516AL,AML,ASL

Asynchronous Silicon Gate CMOS LSI
2048 WORDS x 8 BITS CMOS STATIC RAMS**General Description**

The LC3516A series are fully asynchronous silicon gate CMOS static RAMs organized as 2048 words x 8 bits.

The LC3516A series have two chip enable inputs: $\overline{CE1}$ for high-speed memory access and $\overline{CE2}$ for low standby current mode being valid at the time of battery backup.

The LC3516A series have a full CMOS circuit configuration. Since the current dissipation is low at the data retention mode or standby mode, they are especially suited for use in memory systems, battery-powered portable systems whose power dissipation must be minimized.

The LC3516AL/AML/ASL guarantee a maximum standby current of 1 μ A at 60°C.

Features

- . Address access time (t_{AA})
 - 100ns(max): LC3516A-10/AL-10/AM-10/AML-10/AS-10/ASL-10
 - 120ns(max): LC3516A-12/AL-12/AM-12/AML-12/AS-12/ASL-12
 - 150ns(max): LC3516A-15/AL-15/AM-15/AML-15/AS-15/ASL-15
- . Low standby current

0.2 μ A(max) / Ta=25°C	}	LC3516AL-10/12/15, LC3516AML-10/12/15,
1.0 μ A(max) / Ta=60°C		LC3516ASL-10/12/15
5.0 μ A(max) / Ta=60°C		LC3516A-10/12/15, LC3516AM-10/12/15,
30 μ A(max) / Ta=85°C		LC3516AS-10/12/15
- . Single 5V supply: 5V \pm 10%
- . Data retention supply voltage: 2.0 to 5.5V
- . No clock required (Fully static memory)
- . Directly TTL compatible: All inputs and outputs
- . Common data input and output using 3-state outputs
- . Package

Dual-in-line plastic package	:LC3516A,AL
Miniflat package	:LC3516AM,AML
Dual-in-line slim plastic package:	LC3516AS,ASL

The application circuit diagrams and circuit constants herein are included as an example and provide no guarantee for designing equipment to be mass-produced.

The information herein is believed to be accurate and reliable. However, no responsibility is assumed by SANYO for its use, nor for any infringements of patents or other rights of third parties which may result from its use.

LC3516A,AL
[DIP24(600mil)]

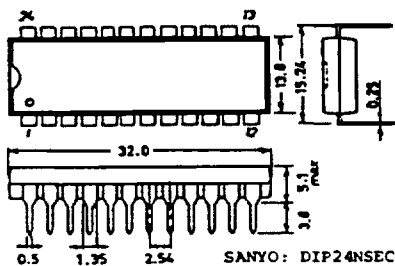
Case Outline 3072-D24NSEC
(unit:mm)

LC3516AM,AML
[MFP24(375mil)]

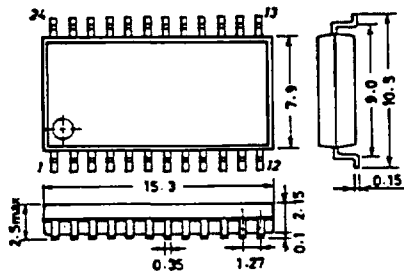
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LC3516AS,ASL
[DIP24Slim(300mil)]

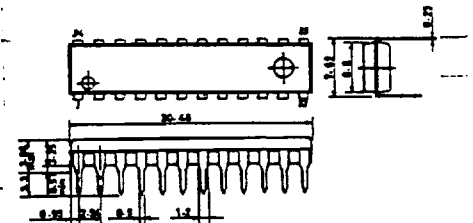
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(unit:mm)



SANYO : DIP24NSEC



SANYO : MFP24



SANYO : DIP24SlimNSEC

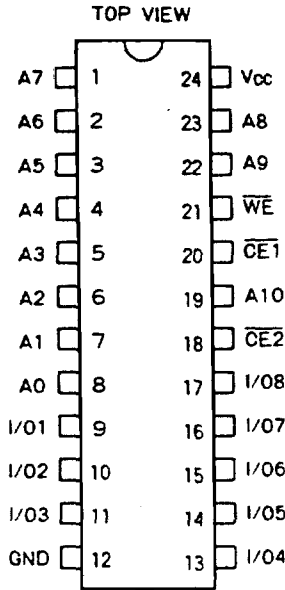
These specifications are subject to change without notice.

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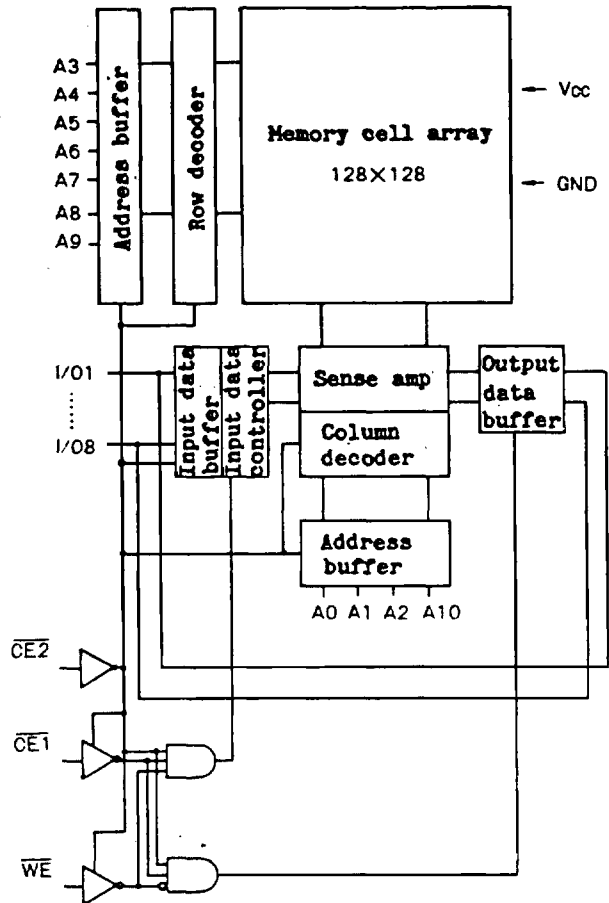
S1Y05020

Pin Assignment

Block Diagram



A0 to A10 Address input
 WE Read/write control input
 CE1 Chip enable input
 CE2 Chip enable input
 I/O1 to I/O8 Data input/output
 V_{CC}/GND Power supply pin



Function Table

Mode	CE2	CE1	WE	I/O	Supply Current
Read Cycle	L	L	H	Data output	I _{CCA}
Write Cycle	L	L	L	Data input	I _{CCA}
Nonselect	L	H	X	High impedance	I _{CCA}
Nonselect	H	X	X	High impedance	I _{CCS}

X:H or L

Absolute Maximum Ratings

Parameter	Symbol	Condition	Limits	unit
Maximum Supply Voltage	V _{CCmax}		+7.0	V
Input Pin Voltage	V _{IN}		-0.3 to V _{CC} +0.3	V
I/O Pin Voltage	V _{I/O}		-0.3 to V _{CC} +0.3	V
Operating Temperature	Topg		-30 to +85	°C
Storage Temperature	Tstg		-55 to +125	°C

DC Allowable Operating Conditions at Ta=-30 to +85°C

Parameter	Symbol	min	typ	max	unit
Supply Voltage	V _{CC}	4.5	5.0	5.5	V
Input "H"-Level Voltage	V _{IH}	2.2		V _{CC} +0.3	V
Input "L"-Level Voltage	V _{IL}	-0.3		0.8	V

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DC Electrical Characteristics at Ta=-30 to +85°C, V_{CC}=5V±10%

Parameter	Symbol	Conditions	min	typ*	max	unit
Input Leak Current	I _{LI}	V _{IN} =0 to V _{CC}	-1.0		1.0	uA
I/O Leak Current	I _{LO}	V _{CE1} or V _{CE2} =V _{IH} , V _{I/O} =0 to V _{CC}	-5.0		5.0	uA
Supply Current(DC)	I _{CCA1}	V _{CE2} =0V, V _{IN} =V _{CC} /GND, I _{I/O} =0mA		30	55	mA
	I _{CCA2}	V _{CE2} =V _{IL} , V _{IN} =V _{IH} /V _{IL} , I _{I/O} =0mA		40	70	mA
Average Supply Current	I _{CCA3}	cycle=min, duty=100%, I _{I/O} =0mA		50	80	mA
Standby Supply Current	I _{CCS1}	V _{CE2} =V _{CC} -0.2V, LC3516A/ V _{IN} =0 to V _{CC} AM/AS Ta=60°C			5.0	uA
		LC3516AL/ Ta=85°C			30	uA
		AML/AMS Ta=25°C			0.2	uA
		AML/AMS Ta=60°C			1.0	uA
Output "H"-Level Voltage	V _{OH}	I _{CCS2} V _{CE2} =V _{IH} , V _{IN} =0 to V _{CC} I _{OH} =-1.0mA		2.4	3.0	V
Output "L"-Level Voltage	V _{OL}	I _{OL} =2.0mA			0.4	V

* Reference value at V_{CC}=5.0V, Ta=+25°C

Input/Output Capacitance at Ta=+25°C, f=1kHz

Parameter	Symbol	Condition	min	typ	max	unit
Input/Output Capacitance	C _{I/O}	V _{I/O} =0V			10	pF
Input Capacitance	C _{IN}	V _{IN} =0V			5	pF

AC Electrical Characteristics Ta=-30 to +85°C, V_{CC}=5V±10%

AC Test Conditions

Input pulse voltage level: 0.6V, 2.4V

Input rise/fall time: 5ns

Input/output timing level: Input "H" level V_{IH}=2.2V, Output "H" level V_{OH}=2.2V
Input "L" level V_{IL}=0.8V, Output "L" level V_{OL}=0.8V

Output load: 1TTL gate + C_L=100pF

Read Cycle

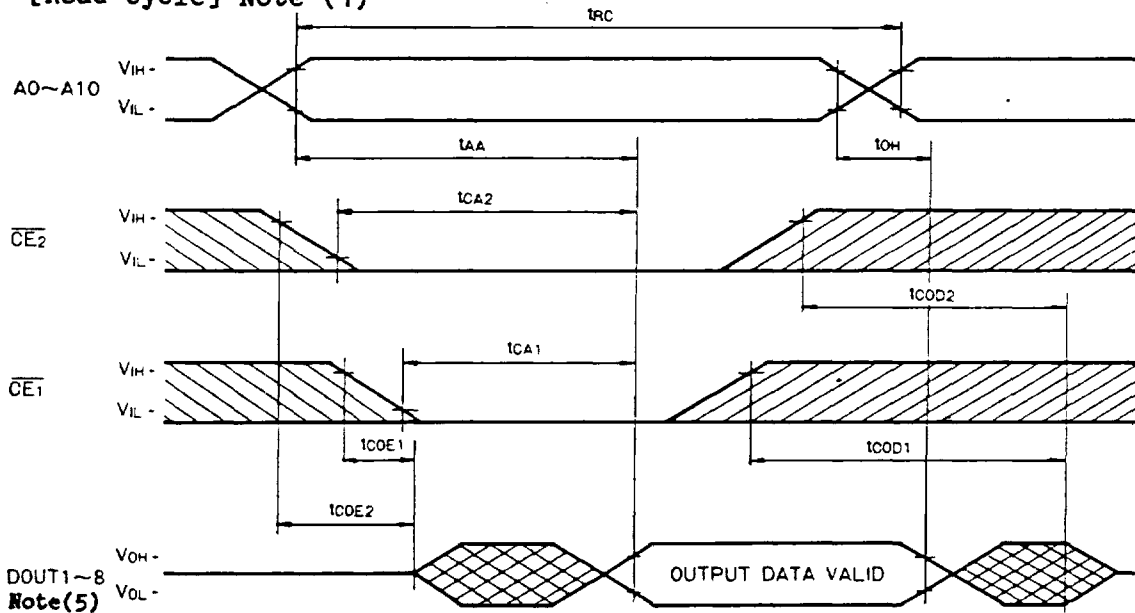
Parameter	Symbol	LC3516A/AM/		LC3516A/AM/		LC3516A/AM/		unit
		AS-10	AS-12	AS-12	AS-15	AS-15		
		LC3516AL/	LC3516AL/	LC3516AL/	LC3516AL/	LC3516AL/		
		AML/ASL-10	AML/ASL-12	AML/ASL-12	AML/ASL-15	AML/ASL-15		
		min	max	min	max	min	max	
Read Cycle Time	t _{RC}	100		120		150		ns
Address Access Time	t _{AA}		100		120		150	ns
CE1 Access Time	t _{CA1}		60		70		80	ns
CE2 Access Time	t _{CA2}		100		120		150	ns
Output Hold Time	t _{OH}	5		5		5		ns
CE1-Output Enable Time	t _{COE1}	5		5		5		ns
CE2-Output Enable Time	t _{COE2}	5		5		10		ns
CE1-Output Disable Time	t _{COD1}		35		40		50	ns
CE2-Output Disable Time	t _{COD2}		35		40		50	ns

Write Cycle

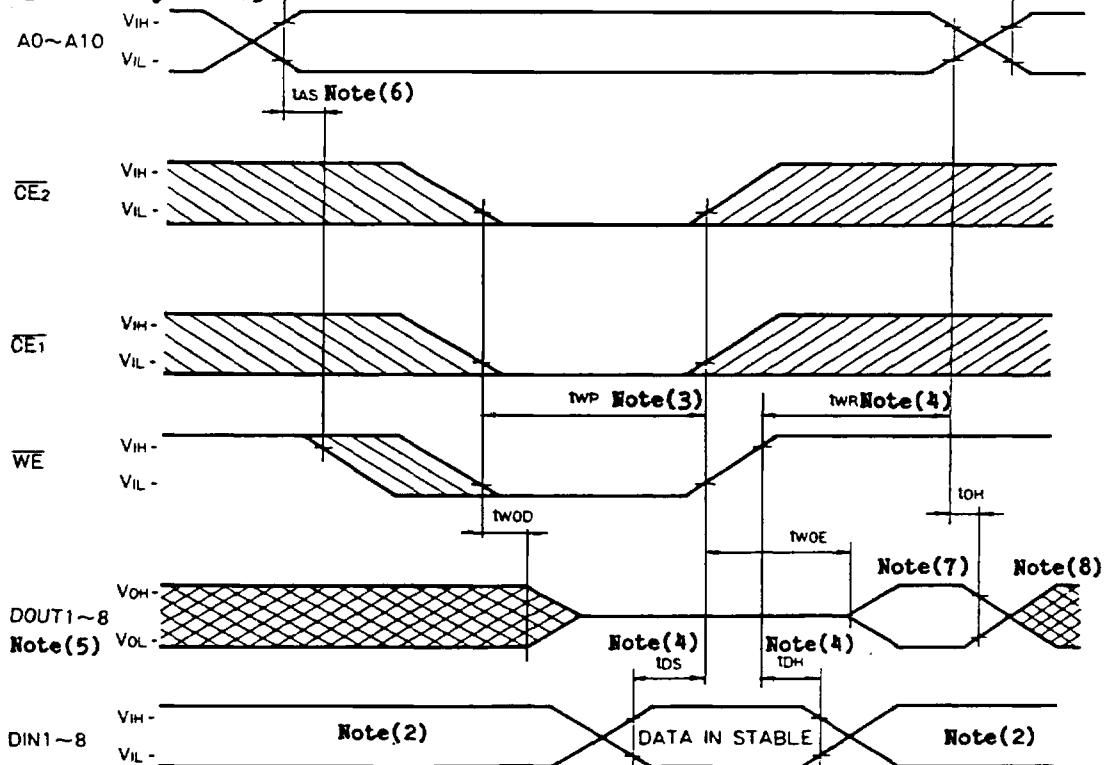
Parameter	Symbol	LC3516A/AM/ AS-10		LC3516A/AM/ AS-12		LC3516A/AM/ AS-15		unit
		min	max	min	max	min	max	
Write Cycle Time	t_{WC}	100		120		150		ns
Address Setup Time	t_{AS}	0		0		0		ns
Write Pulse Width	t_{WP}	75		95		120		ns
Write Recovery Time	t_{WR}	10		10		10		ns
Data Setup Time	t_{DS}	50		60		70		ns
Data Hold Time	t_{DH}	0		0		0		ns
\overline{WE} -Output Enable Time	t_{WOE}	5		5		5		ns
\overline{WE} -Output Disable Time	t_{WOD}		35		40		50	ns

Timing Chart

[Read Cycle] Note (1)

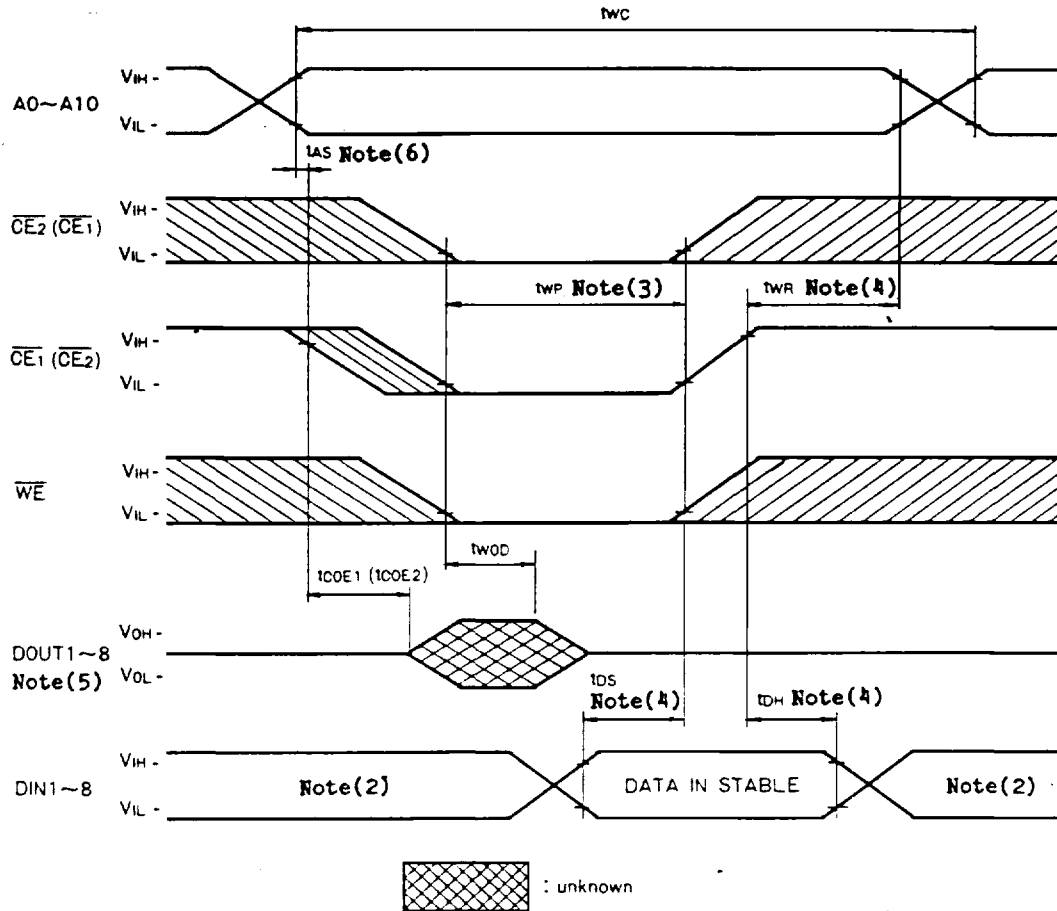


[Write Cycle 1]



 : unknown

[Write Cycle 2]



- Note) (1) \overline{WE} must be high during read cycle.
- (2) When D_{OUT} is in the output state, no opposite polarity signal must be applied externally.
- (3) A write occurs during the overlap of a low $\overline{CE1}$, $\overline{CE2}$ and a low \overline{WE} .
- (4) t_{WR} , t_{DS} , t_{DH} are referenced to the earliest going high of $\overline{CE1}$, or $\overline{CE2}$, or \overline{WE} .
- (5) D_{OUT} is in a high impedance state when $\overline{CE1}$ is high or $\overline{CE2}$ is high or \overline{WE} is low.
- (6) t_{AS} is referenced to the point at which all of $\overline{CE1}$, $\overline{CE2}$, \overline{WE} go low.
- (7) D_{OUT} has the same polarity as write data of this write cycle.
- (8) D_{OUT} is the read-out data of the next address.

Data Retention Characteristics $T_a = -30$ to $+85^\circ C$

Parameter	Symbol	Conditions	min	typ	max	unit
Data Retention Supply Voltage	V_{DR}	$V_{CE2} = V_{CC}, V_{IN} = 0$ to V_{CC}	2.0		5.5	V
Data Retention Supply Current	I_{CCDR}	$V_{CE2} = V_{CC}$ $V_{CC} = 3.0V$ $V_{IN} = 0$ to V_{CC}				
		LC3516A/ AM/AS		$T_a = 60^\circ C$		4.0 μA
				$T_a = 85^\circ C$		20 μA
		LC3516AL/ AML/ASL		$T_a = 25^\circ C$		0.2 μA
				$T_a = 60^\circ C$		1.0 μA
$\overline{CE2}$ Setup Time	t_{CDR}			0		μs
$\overline{CE2}$ Hold Time	t_R			t_{RC} Note(1)		μs

Note) (1) t_{RC} = Read cycle time.

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